

Si NPN TRANSISTOR—D2012

DESCRIPTION AND FEATURES

*Collector-Emmitter voltage: $BV_{CBO}=60V$

*Collector current up to 3A

*High h_{FE} linearity

PIN CONFIGURATIONS

PIN	SYMBOL
1	Emitter
2	Collector
3	Base

ABSOLUTE MAXIMUM RATINGS (Tamb=25)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	BV_{CBO}	60	V
Collector-Emmitter Voltage	BV_{CEO}	50	V
Emmitter-Base Voltage	BV_{EBO}	7	V
Collector Dissipation	Tcase=25	30	W
	Tamb=25	1.5	W
Collector Current	DC	I_{CM}	3
	Pulse	I_{cp}	7
Base Current	I_B	0.6	A
Junction Temperature	T_j	+150	
Storage Temperature	T_{stg}	-55 ~ +150	

ELECTRICAL CHARACTERISTICS (Tamb=25 ,all voltage referenced to GND Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50V, I_E=0$			100	nA
Emmitter Cut-Off Current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	nA
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=20mA$	30	200		
	h_{FE2}	$V_{CE}=5V, I_C=0.5A$	100		400	
Collector-Emmitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=0.3A$		0.3	0.5	V
Base-Emmitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2A, I_B=0.2A$		1.0	2.0	V
Current Gain Bandwidth Product	f_T	$V_{CE}=5V, I_C=0.1A$		5		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		80		pF

CLASSIFICATION OF h_{FE}

RANK	Q	P	E
RANGE	100 ~ 200	160 ~ 320	200 ~ 400

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